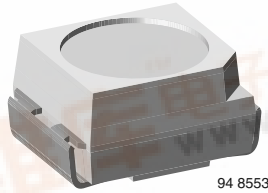


# VSMG3700

Vishay Semiconductors



## High Speed Infrared Emitting Diode, RoHS Compliant, 850 nm, GaAlAs Double Hetero



### FEATURES

- Package type: surface mount
- Package form: PLCC-2
- Dimensions (L x W x H in mm): 3.5 x 2.8 x 1.75
- Peak wavelength:  $\lambda_p = 850$  nm
- High reliability
- High radiant power
- High radiant intensity
- Angle of half intensity:  $\phi = \pm 60^\circ$
- Low forward voltage
- Suitable for high pulse current operation
- High modulation band width:  $f_c = 18$  MHz
- Good spectral matching with Si photodetectors
- Floor life: 4 weeks, MSL 2a, acc. J-STD-020
- Lead (Pb)-free reflow soldering
- Lead (Pb)-free component in accordance with RoHS 2002/95/EC and WEEE 2002/96/EC



RoHS COMPLIANT

### DESCRIPTION

VSMG3700 is an infrared, 850 nm emitting diode in GaAlAs double hetero (DH) technology with high radiant power and high speed, molded in a PLCC-2 package for surface mounting (SMD).

### APPLICATIONS

- Infrared radiation source for operation with CMOS cameras (illumination)
- High speed IR data transmission

PRODUCT SUMMARY				
COMPONENT	$I_e$ (mW/sr)	$\phi$ (deg)	$\lambda_p$ (nm)	$t_r$ (ns)
VSMG3700	10	$\pm 60$	850	20

**Note**

Test conditions see table "Basic Characteristics"

ORDERING INFORMATION			
ORDERING CODE	PACKAGING	REMARKS	PACKAGE FORM
VSMG3700-GS08	Tape and reel	MOQ: 7500 pcs, 1500 pcs/reel	PLCC-2
VSMG3700-GS18	Tape and reel	MOQ: 8000 pcs, 8000 pcs/reel	PLCC-2

**Note**

MOQ: minimum order quantity

ABSOLUTE MAXIMUM RATINGS				
PARAMETER	TEST CONDITION	SYMBOL	VALUE	UNIT
Reverse voltage		$V_R$	5	V
Forward current		$I_F$	100	mA
Peak forward current	$t_p/T = 0.5, t_p = 100 \mu s$	$I_{FM}$	200	mA
Surge forward current	$t_p = 100 \mu s$	$I_{FSM}$	1	A
Power dissipation		$P_V$	180	mW





ABSOLUTE MAXIMUM RATINGS				
PARAMETER	TEST CONDITION	SYMBOL	VALUE	UNIT
Junction temperature		$T_j$	100	°C
Operating temperature range		$T_{amb}$	- 40 to + 85	°C
Storage temperature range		$T_{stg}$	- 40 to + 100	°C
Soldering temperature	acc. figure 8, J-STD-020	$T_{sd}$	260	°C
Thermal resistance junction/ambient	J-STD-051, soldered on PCB	$R_{thJA}$	250	K/W

**Note**

$T_{amb} = 25\text{ }^\circ\text{C}$ , unless otherwise specified

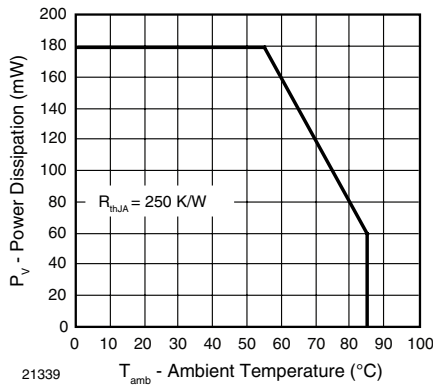


Fig. 1 - Power Dissipation Limit vs. Ambient Temperature

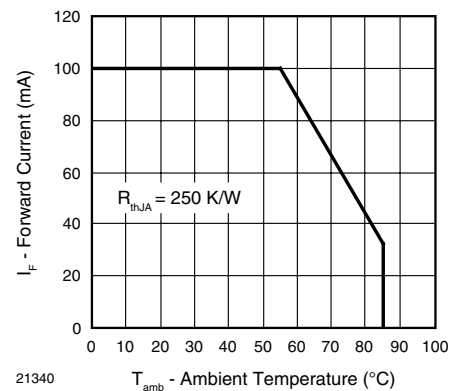


Fig. 2 - Forward Current Limit vs. Ambient Temperature

BASIC CHARACTERISTICS						
PARAMETER	TEST CONDITION	SYMBOL	MIN.	TYP.	MAX.	UNIT
Forward voltage	$I_F = 100\text{ mA}$ , $t_p = 20\text{ ms}$	$V_F$		1.5	1.8	V
	$I_F = 1\text{ A}$ , $t_p = 100\text{ }\mu\text{s}$	$V_F$		2.3		V
Temperature coefficient of $V_F$	$I_F = 1\text{ mA}$	$TK_{V_F}$		- 1.8		mV/K
Reverse current	$V_R = 5\text{ V}$	$I_R$			10	$\mu\text{A}$
Junction capacitance	$V_R = 0\text{ V}$ , $f = 1\text{ MHz}$ , $E = 0$	$C_j$		125		pF
Radiant intensity	$I_F = 100\text{ mA}$ , $t_p = 20\text{ ms}$	$I_e$	6	10	22	mW/sr
	$I_F = 1\text{ A}$ , $t_p = 100\text{ }\mu\text{s}$	$I_e$		100		mW/sr
Radiant power	$I_F = 100\text{ mA}$ , $t_p = 20\text{ ms}$	$\phi_e$		40		mW
Temperature coefficient of $\phi_e$	$I_F = 100\text{ mA}$	$TK_{\phi_e}$		- 0.35		%/K
Angle of half intensity		$\varphi$		$\pm 60$		deg
Peak wavelength	$I_F = 100\text{ mA}$	$\lambda_p$		850		nm
Spectral bandwidth	$I_F = 100\text{ mA}$	$\Delta\lambda$		40		nm
Temperature coefficient of $\lambda_p$	$I_F = 100\text{ mA}$	$TK_{\lambda_p}$		0.25		nm/K
Rise time	$I_F = 100\text{ mA}$	$t_r$		20		ns
Fall time	$I_F = 100\text{ mA}$	$t_f$		13		ns
Cut-off frequency	$I_{DC} = 70\text{ mA}$ , $I_{AC} = 30\text{ mA pp}$	$f_c$		18		MHz
Virtual source diameter		$d$		0.44		mm

**Note**

$T_{amb} = 25\text{ }^\circ\text{C}$ , unless otherwise specified

**BASIC CHARACTERISTICS**

$T_{amb} = 25\text{ }^{\circ}\text{C}$ , unless otherwise specified

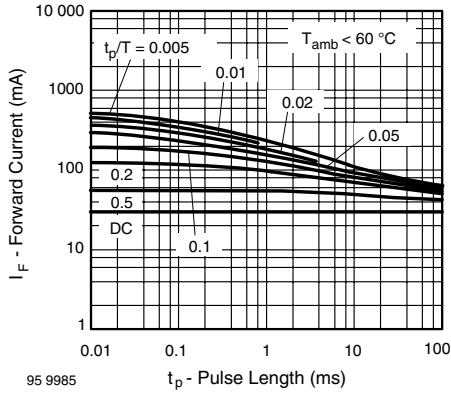


Fig. 3 - Pulse Forward Current vs. Pulse Duration

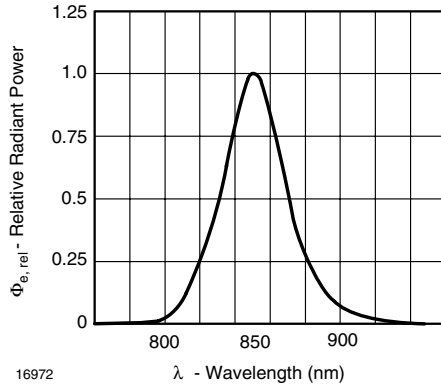


Fig. 6 - Relative Radiant Power vs. Wavelength

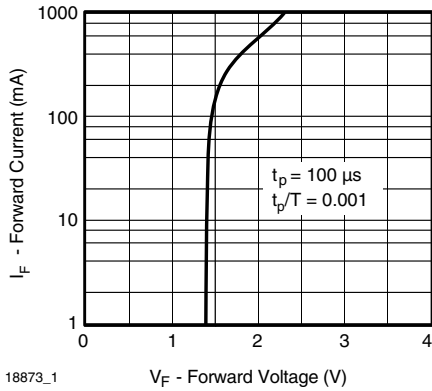


Fig. 4 - Forward Current vs. Forward Voltage

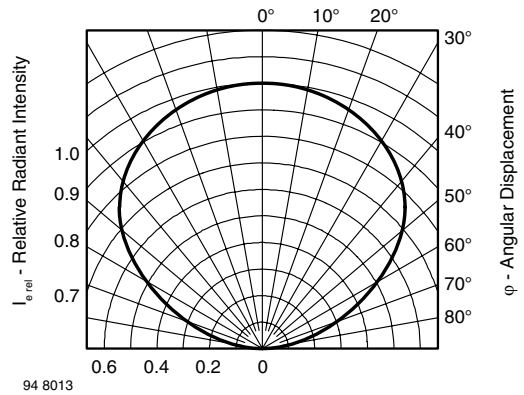


Fig. 7 - Relative Radiant Intensity vs. Angular Displacement

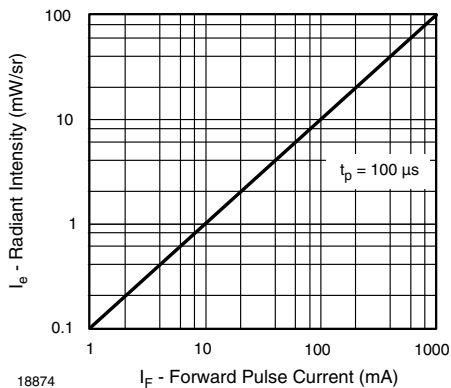
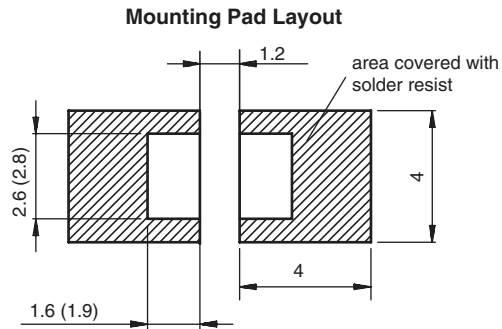
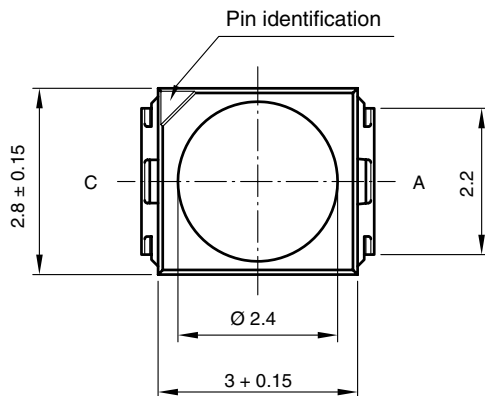
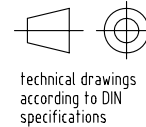
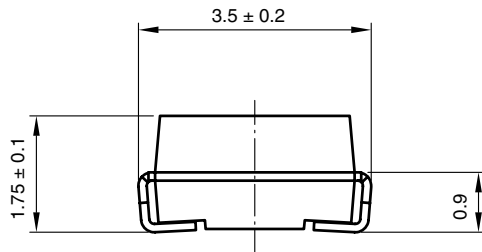


Fig. 5 - Radiant Intensity vs. Forward Current



**PACKAGE DIMENSIONS** in millimeters



Drawing-No.: 6.541-5067.01-4  
 Issue: 4; 30.07.07  
 20541

**SOLDER PROFILE**

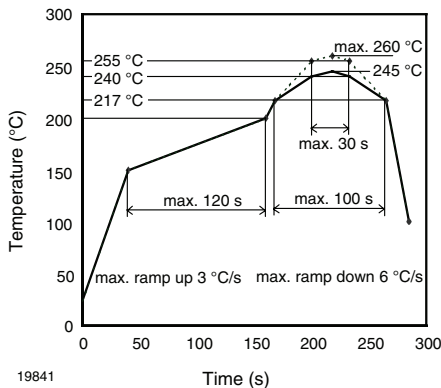


Fig. 8 - Lead (Pb)-free Reflow Solder Profile acc. J-STD-020D

**DRYPACK**

Devices are packed in moisture barrier bags (MBB) to prevent the products from moisture absorption during transportation and storage. Each bag contains a desiccant.

**FLOOR LIFE**

Floor life (time between soldering and removing from MBB) must not exceed the time indicated on MBB label:  
 Floor life: 4 weeks  
 Conditions:  $T_{amb} < 30\text{ °C}$ ,  $RH < 60\%$   
 Moisture sensitivity level 2a, acc. to J-STD-020.

**DRYING**

In case of moisture absorption devices should be baked before soldering. Conditions see J-STD-020 or label. Devices taped on reel dry using recommended conditions 192 h at  $40\text{ °C} (+ 5\text{ °C})$ ,  $RH < 5\%$ .

**TAPE AND REEL**

PLCC-2 components are packed in antistatic blister tape (DIN IEC (CO) 564) for automatic component insertion. Cavities of blister tape are covered with adhesive tape.

# VSMG3700

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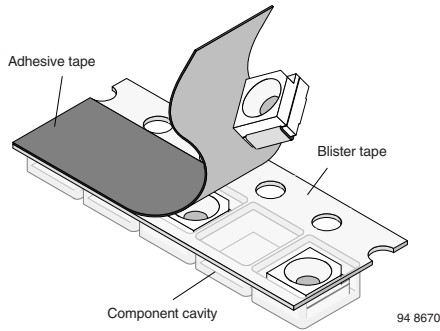


Fig. 9 - Blister Tape

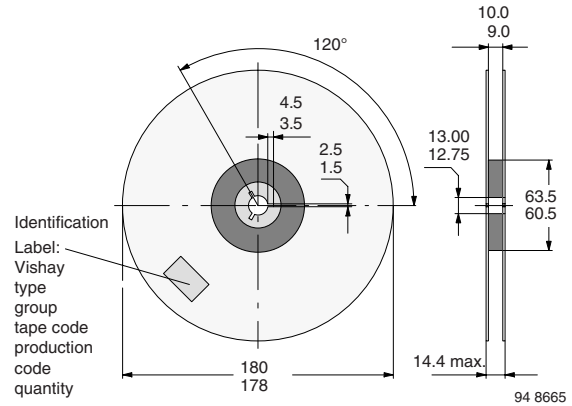


Fig. 12 - Dimensions of Reel-GS08

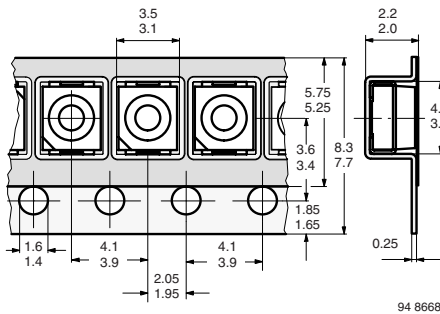


Fig. 10 - Tape Dimensions in mm for PLCC-2

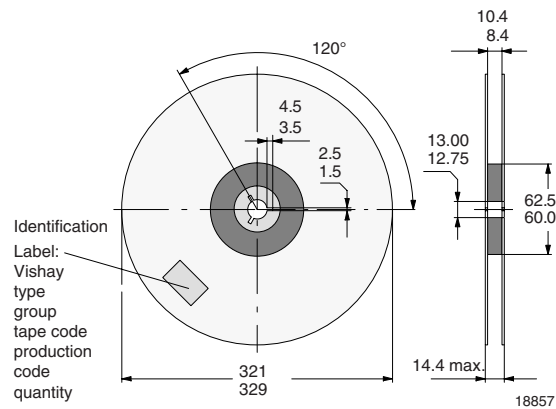


Fig. 13 - Dimensions of Reel-GS18

## MISSING DEVICES

A maximum of 0.5 % of the total number of components per reel may be missing, exclusively missing components at the beginning and at the end of the reel. A maximum of three consecutive components may be missing, provided this gap is followed by six consecutive components.

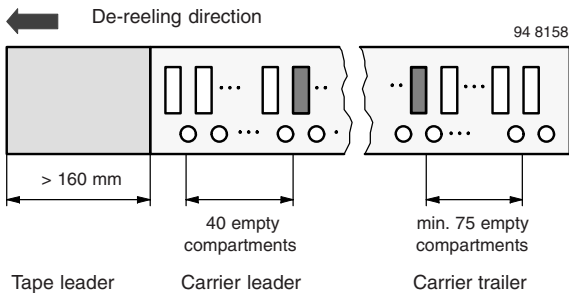


Fig. 11 - Beginning and End of Reel

The tape leader is at least 160 mm and is followed by a carrier tape leader with at least 40 empty compartments. The tape leader may include the carrier tape as long as the cover tape is not connected to the carrier tape. The least component is followed by a carrier tape trailer with a least 75 empty compartments and sealed with cover tape.

## COVER TAPE REMOVAL FORCE

The removal force lies between 0.1 N and 1.0 N at a removal speed of 5 mm/s. In order to prevent components from popping out of the blisters, the cover tape must be pulled off at an angle of 180° with regard to the feed direction.



### Disclaimer

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